## 3.3V/5V, 50 MHz to 200 MHz PECL Clock Synthesizer

#### Description

The NB4N507A is a precision clock synthesizer which generates a very low jitter differential PECL output clock. It produces a clock output based on an integer multiple of an input reference frequency.

The NB4N507A accepts a standard fundamental mode crystal, using Phase-Locked-Loop (PLL) techniques, will produce output clocks up to 200 MHz. In addition, the PLL circuitry will produce a 50% duty cycle square-wave clock output (see Figure 7).

The NB4N507A can be programmed to generate a selection of input reference frequency multiples. An exact 155.52 MHz output clock can be generated from a 19.44 MHz crystal and the x8 multiplier selection. The NB4N507A is intended for low output jitter clock generation.

The PECL outputs are 15 mA open collector and must be DC loaded and AC terminated. See Figures 4 and 6.

#### **Features**

- Input Crystal Frequency of 10 27 MHz
- Enable Usage of Common Low-Cost Crystal
- Differential PECL Output Clock Frequencies up to 200 MHz
- Duty Cycle of 48%/52%
- Operating Range:  $V_{CC} = 3.0 \text{ V}$  to 5.5 V
- Ideal for SONET Applications and Oscillator Manufacturers
- Available in Die Form
- Packaged in 16-Pin Narrow SOIC
- Pb-Free Packages are Available\*

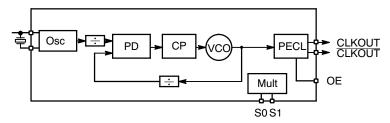


Figure 1. Simplified Logic Block Diagram



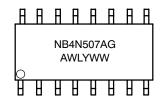
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SOIC-16 D SUFFIX CASE 751B

#### **MARKING DIAGRAM**



A = Assembly Location WL = Wafer Lot

Y = Year WW = Work Week G = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

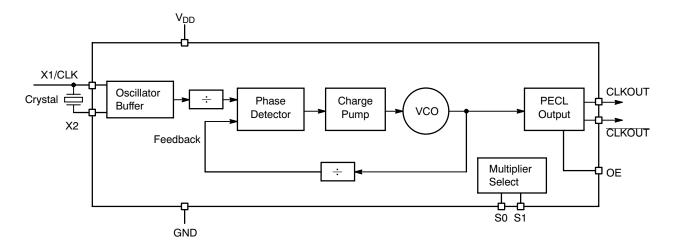


Figure 2. NB4N507A Logic Diagram

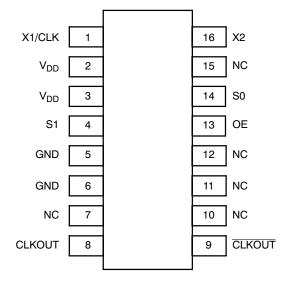


Figure 3. 16-Pin SOIC (Top View)

**Table 1. CLOCK MULTIPLIER SELECT TABLE** 

S1	S0	Multiplier
L	L	9.72X*
L	М	10X
L	Н	12X
М	L	6.25X
M	М	8X
M	Н	5X
Н	L	NA
Н	М	3X
Н	Н	4X

<sup>\*</sup>Example Crystal = 16 MHz, f<sub>CLKOUT</sub> = 155.52 MHz

**Table 2. OE, OUTPUT ENABLE FUNCTION** 

OE	Function
0	Disable
1	Enable

L = GND

 $H = V_{DD}$  M = OPEN

**Table 3. PIN DESCRIPTION** 

Pin # SOIC-16	Name	I/O	Description
1	X1/CLK	Crystal Input	Crystal or Clock Input
2,3	$V_{DD}$	Power Supply	Positive Supply Voltage (3.0 V to 5.5 V)
4	S1	Tri-Level Input	Multiplier Select Pin; When Left Open, Defaults to V <sub>DD</sub> ÷ 2
5,6	GND	Power Supply	Negative Supply Voltage
7,10,11,12, 15	NC	No Connect	Pin 10 does not require an external resistor. The NB4N507A will function with or without a resistor on Pin 10.
8	CLKOUT	PECL Output*	Non-inverted differential PECL clock output.
9	CLKOUT	PECL Output*	Inverted differential PECL clock output.
13	OE	(LV)CMOS/(LV)TTL Input	Output Enable for the CLKOUT/CLKOUT Outputs. Outputs are enabled when HIGH or when left open; OE pin has internal pullup resistor. Disables both outputs when LOW. CLKOUT goes LOW, CLKOUT goes HIGH.
14	S0	Tri-Level Input	Multiplier Select Pin; When Left Open, Defaults to V <sub>DD</sub> ÷ 2
16	X2	Crystal Input	Crystal Input

<sup>\*</sup>The PECL Outputs are 15 mA open collector and must be DC loaded and AC terminated. See Figures 4, 5 and 6.

**Table 4. ATTRIBUTES** 

Charac	Value				
ESD Protection	Human Body Model Machine Model Charged Device Model	> 1 kV > 150 V > 1 kV			
Moisture Sensitivity, Indefinite 7	ime Out of Drypack (Note 1)	Level 1			
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in			
Transistor Count	1145 Devices				
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test					

<sup>1.</sup> For additional information, see Application Note AND8003/D.

**Table 5. MAXIMUM RATINGS** 

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	Positive Power Supply	GND = 0 V		6	V
VI	Input Voltage			GND - $0.5 \le V_{I} \le V_{DD} + 0.5$	V
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-16	100 60	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 2)	SOIC-16	33 to 36	°C/W
T <sub>sol</sub>	Wave Solder Pb Pb-Free	< 3 sec @ 248°C < 3 sec @ 260°C		265 265	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power).

Table 6. DC CHARACTERISTICS ( $V_{DD} = 3.0 \text{ V to } 5.5 \text{ V}$ , GND = 0 V,  $T_A = -40 ^{\circ}\text{C}$  to +85  $^{\circ}\text{C}$  (Note 3))

Symbol	Characteristic		Min	Тур	Max	Unit
I <sub>DD</sub>	Power Supply Current (does not include output load resistor current)	$V_{DD} = 5 V$ $V_{DD} = 3.3 V$	15 10	27 23	35 30	mA mA
V <sub>OH</sub>	Output HIGH Voltage (Notes 5 & 6)	V <sub>DD</sub> = 5 V V <sub>DD</sub> = 3.3 V	3.95 2.57	4.05 2.67	4.15 2.77	V
V <sub>OL</sub>	Output LOW Voltage (Notes 5 & 6)	$V_{DD} = 5 V$ $V_{DD} = 3.3 V$	3.12 1.90	3.20 2.00	3.30 2.10	V
V <sub>IH</sub>	Input HIGH Voltage (Note 4)	S0, S1, X1/CLK OE	V <sub>DD</sub> - 0.5 2.0		V <sub>DD</sub>	V
V <sub>IL</sub>	Input LOW Voltage,(Note 4)	S0, S1, X1/CLK OE	0		0.5 0.8	V
C <sub>x</sub>	Internal Crystal Capacitance, X1 & X2			0		pF
C <sub>in</sub>	Input Capacitance, S0, S1, OE			5.0		pF

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 3. PECL output parameters vary 1:1 with  $V_{DD}$ .
- 4. So and S1 default to  $V_{DD} \div 2$  when left open.

Table 7. AC CHARACTERISTICS ( $V_{DD} = 3.0 \text{ V}$  to 5.5 V, GND = 0 V,  $T_A = -40 ^{\circ}\text{C}$  to  $+85 ^{\circ}\text{C}$  (Note 5))

Symbol	Characteristic		Min	Тур	Max	Unit
f <sub>Xtal</sub>	Crystal Input Frequency (Note 7)		10		27	MHz
f <sub>CLK</sub>	Input Clock Frequency (Note 8)		5		52	MHz
f <sub>OUT</sub>	Output Frequency Range		50		200	MHz
V <sub>out pk-pk</sub>	Output Amplitude		550	680		mV
DC	Clock Output Duty Cycle (Note 8)		48		52	%
PLL <sub>BW</sub>	PLL Bandwidth (Note 8)		10			kHz
t <sub>jitter (pd)</sub>	Period Jitter (RMS, 1σ, 10,000 Cycles)				10	ps
t <sub>jitter (pd)</sub>	Period Jitter (Peak-to-Peak, 10,000 Cycles)				± 20	ps
tr/tf	Output Rise and Fall Times (Note 8)		50	270	500	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 5. PECL outputs loaded with external resistors for proper operation (see Figures 4, 5 and 6).
- 6.  $V_{OH}$  and  $\dot{V}_{OL}$  can be set by the external resistors, which can be modified.
- 7. The crystal should be fundamental mode, parallel resonant. Do not use third overtone. For exact tuning when using a crystal, capacitors should be connected from pins X1 to ground and X2 to ground. The value of these capacitors is given by the following equation, where CL is the specified crystal load capacitance: Crystal caps (pF) = (CL-5) x 2. So, for a crystal with 16 pF load capacitance, use two 22 pF caps, including board trace capacitance (see Figure 7).
- 8. Guaranteed by design and characterization.

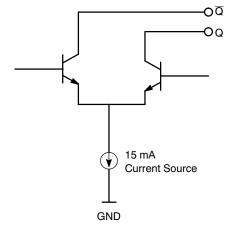


Figure 4. Output Structure

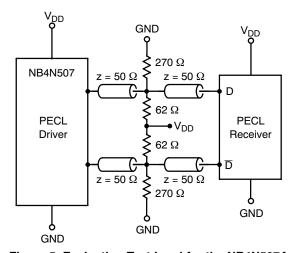


Figure 5. Evaluation Test Load for the NB4N507A

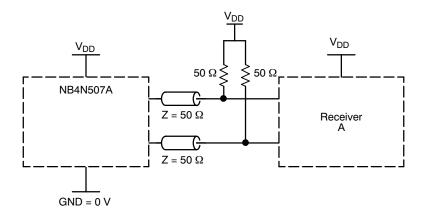


Figure 6. Alternate Termination for Output Driver and Device Evaluation

#### **APPLICATIONS INFORMATION**

High Frequency Differential PECL Oscillators: The NB4N507A, along with a low frequency fundamental mode crystal, can build a high frequency differential PECL output oscillator. For example, a 10 MHz crystal connected to the NB4N507A with the 12X output selected (S1 = 0, S0 = 1) produces a 120 MHz PECL output clock.

#### **Crystal Oscillator Input Interface**

The NB4N507A features an integrated crystal oscillator to minimize system implementation costs. The oscillator circuit is a parallel resonant circuit and thus, for optimum performance, a parallel resonant crystal should be used.

As the oscillator is somewhat sensitive to loading on its inputs, the user is advised to mount the crystal as close to the NB4N507A as possible to avoid any board level parasitics. Surface mount crystals are recommended, but not required.

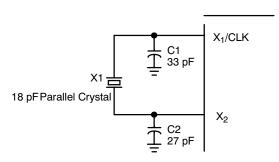


Figure 7. Crystal Input Interface

# **High Frequency VCXO:** The bandwidth of the PLL is guaranteed to be greater than 10 kHz. This means that the PLL will track any modulation on the input with a frequency of less than 10 kHz. By using this property, a low frequency VCXO can be built. The output can then be multiplied by the NB4N507A, thereby producing a high frequency VCXO.

**High Frequency TCXO:** Extending the previous application, an inexpensive, low frequency TCXO can be built and the output frequency can be multiplied using the NB4N507A. Since the output of the chip is phase-locked to the input, the NB4N507A has no temperature dependence, and the temperature coefficient of the combined system is the same as that of the low frequency TCXO.

#### **Decoupling and External Components**

The NB4N507A requires a 0.01  $\mu$ F decoupling capacitor to be connected between  $V_{DD}$  and GND on pins 2 and 5. It must be connected close to the NB4N507A. Other  $V_{DD}$  and GND connections should be connected to those pins, or to the  $V_{DD}$  and GND planes on the board. Another four resistors are needed for the PECL outputs as shown in Figure 4. Suggested values of these resistors are shown, but they can be varied to change the differential pair output swing, and the DC level.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NB4N507AD	SOIC-16	48 Units / Rail
NB4N507ADG	SOIC-16 (Pb-Free)	48 Units / Rail
NB4N507ADR2	SOIC-16	2500 / Tape & Reel
NB4N507ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **Resource Reference of Application Notes**

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPICE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1670/D - The FCL Translator Cycles

AN1672/D - The ECL Translator Guide

AND8090/D - AC Characteristics of ECL Devices

#### **Resource Reference of Application Notes**

AND8001/D - Odd Number Counters Design

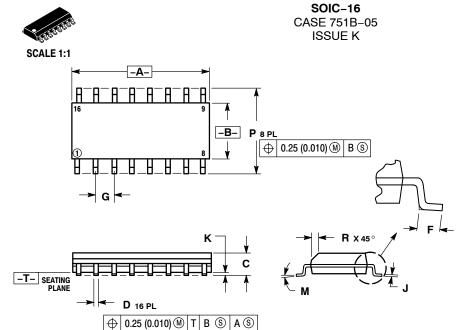
AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices

### **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

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STYLE 5: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, DYE #1 DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #2 SOURCE, #3 GATE, #2 SOURCE, #1 SOURCE, #1	3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	STYLE 7: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	SOURCE N-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT SOURCE N-CH		16 0.£	16X 1.12	- 1.27 PITCH

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